

Abstracts

W-Band SPST Transistor Switches

*H. Takasu, F. Sasaki, H. Kawasaki, H. Tokuda and S. Kamihashi. "W-Band SPST Transistor Switches." 1996 *Microwave and Guided Wave Letters* 6.9 (Sep. 1996 [MGWL]): 315-316.*

A single-pole, single-throw (SPST) transistor switch has been developed. Three types of switches, that is, GaAs MESFET, AlGaAs/GaAs HEMT, and pseudomorphic HEMT (PM-HEMT), have been fabricated, and the performances at W-band are compared. To reduce on-state resistance and off-state capacitance, a gate length was varied as a parameter. Moreover, an inductance far resonance was installed in parallel to the off-state capacitance between source and drain to obtain a high isolation. A relatively low insertion loss of 1.6 dB and a high isolation over 20 dB at W-band have been obtained from the 0.8- μ m gate length PM-HEMT.

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